

## ABSTRACT

A reflective mask and a reflective mask blank that can form a fine mask pattern with high accuracy in shape, achieve a sufficient contrast in a pattern inspection, and enable a pattern transfer with high accuracy. On a substrate (11), a multilayer reflective film (12) for reflecting an exposure light, a buffer layer (13), and an absorber layer for absorbing the exposure light are successively deposited in this order. This absorber layer has a layered structure composed of an uppermost layer (15) and a lower layer (14) other than it. The uppermost layer (15) exhibits a reflectance of 20% or less with respect to a light having an inspection wavelength for use in an inspection of a pattern formed in the absorber layer and further is formed of an inorganic material having a resistance against an etching condition in forming a pattern in the lower layer.